

5/18/06

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030241US1	Application No. 10/689,506		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Huajie CHEN, et al..			
				Filing Date 10/20/2003		Group 2813	
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EXAMINER <i>Ex. JMM</i>				DATE CONSIDERED <i>10/1/06</i>			
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